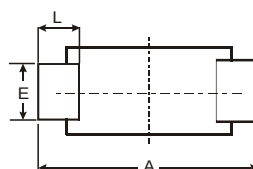
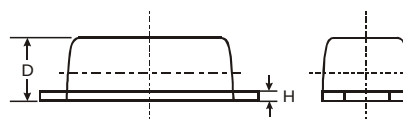
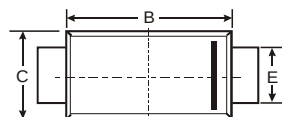
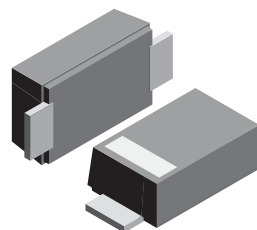


VOLTAGE RANGE: 20 - 100V

CURRENT: 1.0 A

Features

- Schottky Barrier Chip
- Ideally Suited for Automatic Assembly
- Low Power Loss, High Efficiency
- For Use in Low Voltage Application
- Guard Ring Die Construction
- Plastic Case Material has UL Flammability Classification Rating 94V-O



SMAF			
Dim	Min	Max	Typ
A	4.75	4.85	4.80
B	3.68	3.72	3.70
C	2.57	2.63	2.60
D	0.097	1.03	1.00
E	1.38	1.42	1.40
H	0.13	0.17	0.15
L	0.63	0.67	0.65
All Dimensions in mm			

Mechanical Data

- Case: SMAF, Molded Plastic
- Terminals: Solder Plated, Solderable per MIL-STD-750, Method 2026
- Polarity: Color band denotes cathode end
- Mounting Position: Any
- Weight: 0.0018 ounce, 0.064 grams



Maximum Ratings and Electrical Characteristics T_A = 25° C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	SS12F	SS13F	SS14F	SS15F	SS16F	SS18F	SS110F	Unit
Maximum repetitive peak reverse voltage	V _{RRM}	20	30	40	50	60	80	100	V
Maximum RMS voltage	V _{RMS}	14	21	28	35	42	56	70	V
Maximum DC blocking voltage	V _{DC}	20	30	40	50	60	80	100	V
Maximum average forward rectified current at T _L (see fig.1)	I _(AV)	1.0							A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	40.0							A
Maximum instantaneous forward voltage at 1.0A	V _F	0.45	0.55		0.70		0.85		V
Maximum DC reverse current T _A =25°C at rated DC blocking voltage T _A =100°C	I _R	0.5							mA
		6.0			5.0				
Typical junction capacitance (NOTE 1)	C _J	110			90				pF
Typical thermal resistance (NOTE 2)	R _{θJA}	88.0							°C/W
Operating junction temperature range	T _J ,	-65 to +125			-65 to +150				°C
Storage temperature range	T _{STG}	-65 to +150							°C

Note: 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
2. P.C.B. mounted with 0.2x0.2" (5.0x5.0mm) copper pad areas

RATINGS AND CHARACTERISTIC CURVES SS12F THRU SS110F

